



Docket No.: 53074-025

#9/1A
10/24/03
PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of

Tetsuzo UEDA

Serial No.: 09/904,129

Group Art Unit: 1765

Filed: July 11, 2001

Examiner: Matthew J. Song

For: BUFFER LAYER AND GROWTH METHOD FOR SUBSEQUENT EPITAXIAL
GROWTH OF III-V NITRIDE SEMICONDUCTORS

AMENDMENT

Commissioner for Patents
Washington, DC 20231

Sir:

In response to the Office Action dated October 23, 2002, having a three-month shortened statutory period for response set to expire on January 23, 2003, reconsideration of the above-identified application is respectfully requested in view of the following amendment and remarks.

IN THE SPECIFICATION

Please replace the paragraph beginning on page 6, line 11 with the following paragraph:

A, --In an exemplary embodiment, the buffer layer 230 may be formed by spin coating a liquid which contains metal and oxygen. Then, the wafer is annealed in a gas atmosphere in which the gas contains oxygen as an element.--